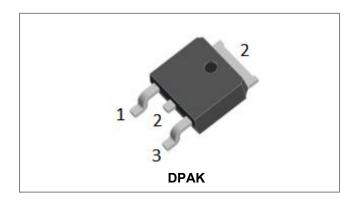


MBRD10200

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MBRD10200 SCHOTTKY RECTIFIER



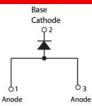
Features

- 175℃ T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Circuit Diagram



Maximum Ratings:

Characteristics	Symbol	Condition Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=105°C, rectangular wave form	10	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	150	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.85	0.90	V
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.75	0.85	V
Reverse Current *	I _{R1}	$@V_R$ = rated V_{R} , T_J = 25 °C	0.0002	1.0	mA
	I _{R2}	$@V_R = rated V_R, T_J = 125 \circ C$	0.03	50	mA
Junction Capacitance	Ст	@V _R = 5.0V, T _C = 25 °C f _{SIG} = 1MHz	120	300	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μ s, duty cycle < 2%

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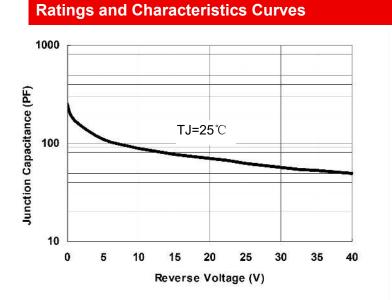
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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{0JC}	-	6	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			





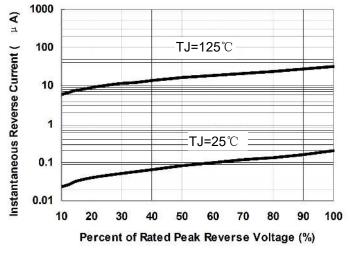


Fig.2-Typical Reverse Characteristics

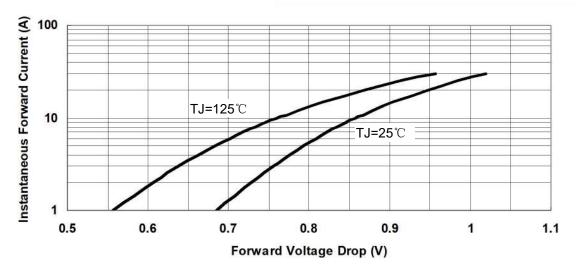


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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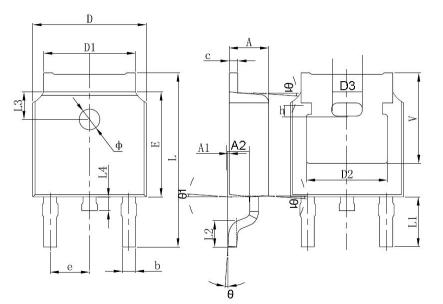
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Mechanical Dimensions DPAK



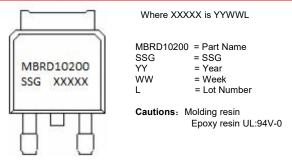
SYMBOL		imensions millimeters		
	Min.	Тур.	Max.	
A	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
с	0.46	-	0.89	
D	6.35	-	6.73	
D2	4.32	-	-	
E	5.97	6.10	6.22	
е	2.29BSC			
L	9.40	-	10.41	
L2	1.40	1.52	1.78	
L4	-	-	1.02	
Θ	0°	-	10°	
V	5.21	-	-	

Ordering Information

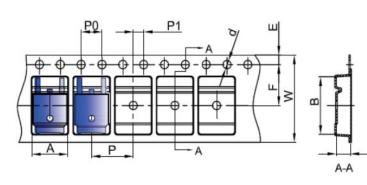
Device	Package	Shipping
MBRD10200	DPAK (Pb-Free)	2500pcs / reel
MBRD10200TR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Carrier Tape Specification DPAK



SYMBOL	Millimeters			
STWBUL	Min.	Max.		
A	6.80	7.00		
В	10.40	10.60		
С	2.60	2.80		
d	Φ1.45	Φ1.65		
E	1.65	1.85		
F	7.40	7.60		
P0	3.90	4.10		
Р	7.90	8.10		
P1	1.90	2.10		
W	15.90	16.30		

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